

Mariko Suzuki

List of Publications by Year in descending order

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15
papers

745
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623734

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16
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16
docs citations

16
times ranked

530
citing authors

#	ARTICLE	IF	CITATIONS
1	Diamond for Electronics: Materials, Processing and Devices. <i>Materials</i> , 2021, 14, 7081.	2.9	23
2	Low-temperature thermionic emission from nitrogen-doped nanocrystalline diamond films on n-type Si grown by MPCVD. <i>Diamond and Related Materials</i> , 2009, 18, 1274-1277.	3.9	35
3	Application of diamond film to cold cathode fluorescent lamps for LCD backlighting. <i>Diamond and Related Materials</i> , 2006, 15, 1998-2000.	3.9	11
4	Electrical characteristics of n-type diamond Schottky diodes and metal/diamond interfaces. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 3128-3135.	1.8	54
5	n-Type doping of diamond. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 3358-3366.	1.8	42
6	Electrical properties of B-related acceptor in B-doped homoepitaxial diamond layers grown by microwave plasma CVD. <i>Diamond and Related Materials</i> , 2004, 13, 198-202.	3.9	28
7	Electrical characterization of phosphorus-doped n-type homoepitaxial diamond layers by Schottky barrier diodes. <i>Applied Physics Letters</i> , 2004, 84, 2349-2351.	3.3	50
8	Doping characteristics and electrical properties of Mg-doped AlGaN grown by atmospheric-pressure MOCVD. <i>Journal of Crystal Growth</i> , 1998, 189-190, 511-515.	1.5	93
9	p-type conduction in as-grown Mg-doped GaN grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 1998, 72, 1748-1750.	3.3	40
10	Room Temperature Pulsed Operation of Nitride Based Multi-Quantum-Well Laser Diodes with Cleaved Facets on Conventional C-Face Sapphire Substrates. <i>Japanese Journal of Applied Physics</i> , 1996, 35, L1315-L1317.	1.5	219
11	Reduction of residual oxygen incorporation and deep levels by substrate misorientation in InGaAlP alloys. <i>Journal of Crystal Growth</i> , 1993, 133, 303-308.	1.5	30
12	Effects of Growth Parameters on Oxygen Incorporation into InGaAlP Grown by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 1993, 32, 498-501.	1.5	24
13	Effects of residual impurities on Zn electrical activity in Zn-doped InGaAlP grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 1992, 123, 181-187.	1.5	17
14	Effects of substrate misorientation on doping characteristics and band gap energy for InGaAlP crystals grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 1991, 113, 127-130.	1.5	51
15	Electrical characterization of Si-donor-related shallow and deep states in InGaAlP alloys grown by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 1991, 115, 498-503.	1.5	27